HEF4011B

Quad 2-input NAND gate

Rev. 5 — 21 November 2011

Product data sheet

1. General description

The HEF4011B is a quad 2-input NAND gate. The outputs are fully buffered for the highest noise immunity and pattern insensitivity to output impedance.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

2. Features and benefits

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from –40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B
- Inputs and outputs are protected against electrostatic effects

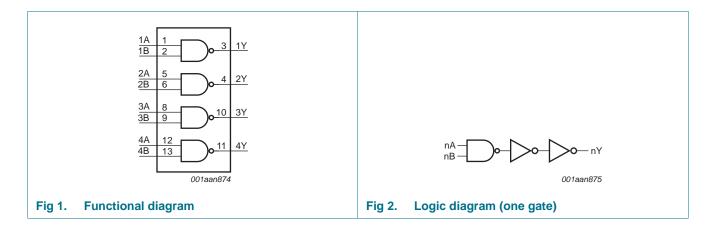
3. Ordering information

Table 1. Ordering information

All types operate from −40 °C to +125 °C

Type number	Package		
	Name	Description	Version
HEF4011BP	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
HEF4011BT	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1

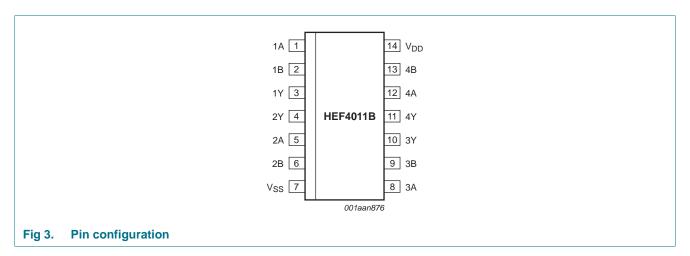
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
nA	1, 5, 8, 12	input
nB	2, 6, 9, 13	input
nY	3, 4, 10, 11	output
V _{SS}	7	ground (0 V)
$\frac{V_{SS}}{V_{DD}}$	14	supply voltage

6. Functional description

Table 3. Function table [1]

Input O		Output
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to $V_{SS} = 0 \text{ V}$ (ground).

	, ,			,
Parameter	Conditions	Min	Max	Unit
supply voltage		-0.5	+18	V
input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
input voltage		-0.5	$V_{DD} + 0.5$	V
output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
input/output current		-	±10	mA
supply current		-	50	mA
storage temperature		-65	+150	°C
ambient temperature		-40	+125	°C
total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to + 125 } ^{\circ}\text{C}$			
	DIP14	<u>[1]</u> -	750	mW
	SO14	[2] _	500	mW
power dissipation	per output	-	100	mW
	supply voltage input clamping current input voltage output clamping current input/output current supply current storage temperature ambient temperature total power dissipation	supply voltage input clamping current $V_{I} < -0.5 \text{ V or } V_{I} > V_{DD} + 0.5 \text{ V}$ input voltage output clamping current $V_{O} < -0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V}$ input/output current supply current storage temperature ambient temperature total power dissipation	supply voltage -0.5 input clamping current $V_{I} < -0.5 \text{ V or } V_{I} > V_{DD} + 0.5 \text{ V} - 0.5$ input voltage -0.5 output clamping current $V_{O} < -0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V} - 0.5$ input/output current $-0.5 \text{ Supply current} -0.5 \text{ Supply current} -0.5$ storage temperature $-0.5 \text{ Storage temperature} -0.5 \text{ Current} -0.5$ ambient temperature $-0.5 \text{ Current} -0.5 \text{ Current} -0.5$ total power dissipation $-0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V} - 0.5 \text{ V} - 0.5 \text{ V} - 0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V} - 0.5 \text{ V} - 0.5 \text{ V} - 0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V} - 0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V} - 0.5 \text{ V or } V_{O} > V_{DD} + 0.5 \text{ V or } V_{O}$	supply voltage -0.5 $+18$ input clamping current $V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$ $ \pm 10$ input voltage -0.5 $V_{DD} + 0.5$ output clamping current $V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$ $ \pm 10$ input/output current $ \pm 10$ supply current $ \pm 50$ storage temperature $ +$ $+$ ambient temperature $ +$ $+$ $+$ total power dissipation $ +$ $+$

^[1] For DIP14 packages: above T_{amb} = 70 °C, P_{tot} derates linearly with 12 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Parameter	Conditions	Min	Тур	Max	Unit
supply voltage		3	-	15	V
input voltage		0	-	V_{DD}	V
ambient temperature	in free air	-40	-	+125	°C
input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
	V _{DD} = 10 V	-	-	0.5	μs/V
	V _{DD} = 15 V	-	-	0.08	μs/V
	supply voltage input voltage ambient temperature	supply voltage input voltage ambient temperature in free air input transition rise and fall rate $ V_{DD} = 5 \text{ V} $ $V_{DD} = 10 \text{ V} $	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	supply voltage $ \begin{array}{ccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

^[2] For SO14 packages: above T_{amb} = 70 °C, P_{tot} derates linearly with 8 mW/K.

9. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$ V; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	-40 °C	T _{amb} =	+25 °C	T _{amb} =	+85 °C	T _{amb} = -	⊦125 °C	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V
V _{OH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level	$V_0 = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mΑ
	output current	V _O = 4.6 V	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mA
		V _O = 9.5 V	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mA
		V _O = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mA
I _{OL}	LOW-level	$V_0 = 0.4 \ V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
	output current	V _O = 0.5 V	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		V _O = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I _I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μΑ
I_{DD}	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μΑ
		combinations;	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μΑ
		$I_O = 0 A$	15 V	-	1.0	-	1.0	-	30.0	-	30.0	μΑ
C _I	input capacitance			-	-	-	7.5	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

 T_{amb} = 25 °C; for waveforms see <u>Figure 4</u>; for test circuit see <u>Figure 5</u>; unless otherwise specified.

Symbol	Parameter	Extrapolation formula[1]	V_{DD}	Min	Тур	Max	Unit
t_{pd}	propagation delay	$28 + 0.55 \times C_L$	5 V	[2] -	55	110	ns
		$14 + 0.23 \times C_L$	10 V	-	25	45	ns
		$12 + 0.16 \times C_L$	15 V	-	20	35	ns
t_{THL}	HL HIGH to LOW output transition tim	$10 + 1.00 \times C_L$	5 V	-	60	120	ns
		$9 + 0.42 \times C_L$	10 V	-	30	60	ns
		$6 + 0.28 \times C_L$	15 V	-	20	40	ns
t _{TLH}	LOW to HIGH output transition time	10 + 1.00 × C _L	5 V	-	60	120	ns
		9 + 0.42 × C _L	10 V	-	30	60	ns
		$6 + 0.28 \times C_L$	15 V	-	20	40	ns

^[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

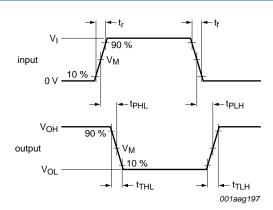
Table 8. Dynamic power dissipation

 $V_{SS} = 0 \text{ V; } t_r = t_f \le 20 \text{ ns; } T_{amb} = 25 \text{ °C.}$

Symbol	Parameter	V_{DD}	Typical formula	Where
P _D dynamic power dissipation	dynamic power dissipation	5 V	$P_D = 1300 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2 (\mu W)$	f _i = input frequency in MHz;
		10 V	$P_D = 6000 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2 (\mu W)$	fo = output frequency in MHz;
P _D dynamic power dissipation		15 V	$P_D = 20100 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2 (\mu W)$	C_L = output load capacitance in pF;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs;
				V _{DD} = supply voltage in V.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

11. Waveforms



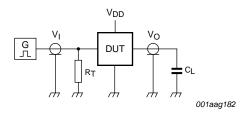
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Propagation delay, output transition time

Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V _M	V _M
5 V to 15 V	0.5V _{DD}	0.5V _{DD}



Test data is given in <u>Table 10</u>.

Definitions for test circuit:

DUT = Device Under Test.

C_L = load capacitance including jig and probe capacitance.

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig 5. Test circuit for measuring switching times

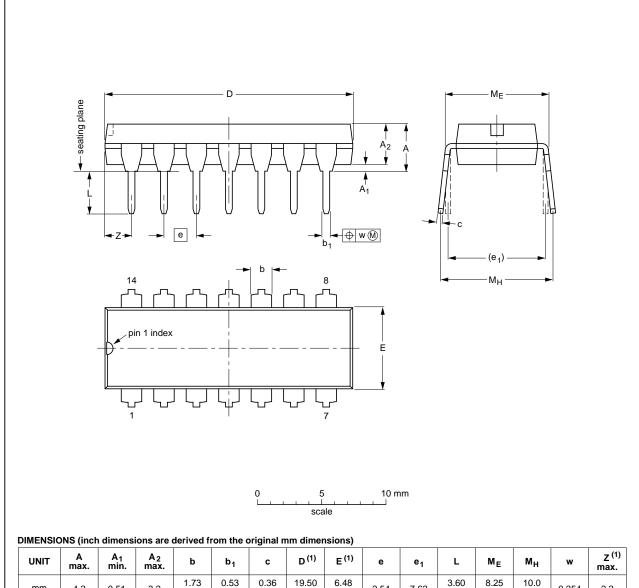
Table 10. Test data

Supply voltage	Input	Load	
V_{DD}	VI	t _r , t _f	CL
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

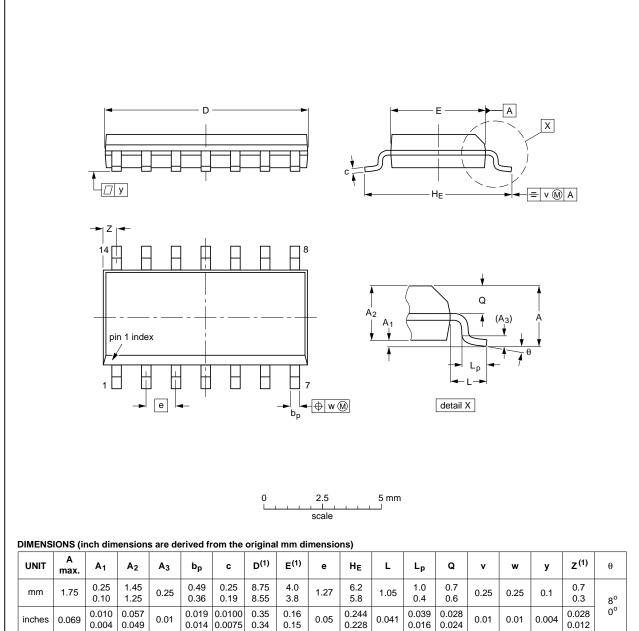
OUTLINE		REFER	RENCES		EUROPEAN ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE			
SOT27-1	050G04	MO-001	SC-501-14			99-12-27 03-02-13			
			•	•			•		

Fig 6. Package outline SOT27-1 (DIP14)

HEF4011B

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



inches

Note 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.0075

0.34

0.15

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

0.228

Package outline SOT108-1 (SO14) Fig 7.

0.004

HEF4011B

0.012

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4011B v.5	20111121	Product data sheet	-	HEF4011B v.4
Modifications:	Legal pagesChanges in '	updated. "General description" and "Fe	eatures and benefits".	
	 Section "App 	olications" removed.		
HEF4011B v.4	20110330	Product data sheet	-	HEF4011B_CNV v.3
HEF4011B_CNV v.3	19950101	Product specification	-	HEF4011B_CNV v.2
HEF4011B_CNV v.2	19950101	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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HEF4011B

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Quad 2-input NAND gate

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